

ABSTRACT OF DISCLOSURE

A monolithic semiconductor optical device with excellent temperature and modulation characteristics and associated method of manufacturing whereby the device has a semiconductor substrate, a semi-insulating buried heterostructure GaInAsP-based DFB laser; and either a buried ridge type AlGaInAs-based EA or a self aligned structure (SAS) AlGaInAs-based EA modulator.

C:\WINDOWS\TEMP\216449US_checked_by_FEC.doc

205TFO" 066449001